

Application Note

Argon ion milling of FIB lift-out samples

Introduction

The high-resolution TEM and combined analytical methods became more and more important in the recent investigations of material science. As a result TEM sample preparation plays an important role in this process. For semiconductor materials the use of focused ion beam (FIB) is a common method in TEM sample preparation at present. However, FIB has some drawbacks, especially in high-resolution TEM (HRTEM) imaging. The high-energy Ga⁺ ions used in FIB create amorphous layer on the sample surface limiting the information that can be obtained from the HRTEM investigations.

The Gentle Mill low-energy Ar⁺ ion milling system has been developed for decreasing and/or eliminating these artifacts in the FIB prepared samples. The report provides some basic instructions for preparing TEM samples by low-energy ion milling of FIB samples.

TEM sample preparation for high-resolution TEM application

FIB sample preparation

The two most common techniques of FIB preparation are the so-called H-bar and Lift-out techniques.

H-bar samples: a slab of material is initially thinned by mechanical polishing down to a thickness of about 50µm. Then FIB is used to cut two trenches, one from each side, leaving between a thin lamella supported by two side bars on the opposite ends.

Lift-out samples: a similar approach is used, however the thin lamella is cut away from the side bars and lifted out from the trench. In-situ lift-out allows the thin lamella to be attached to a grid by FIB welding techniques.

Low-energy ion milling (Gentle Mill)

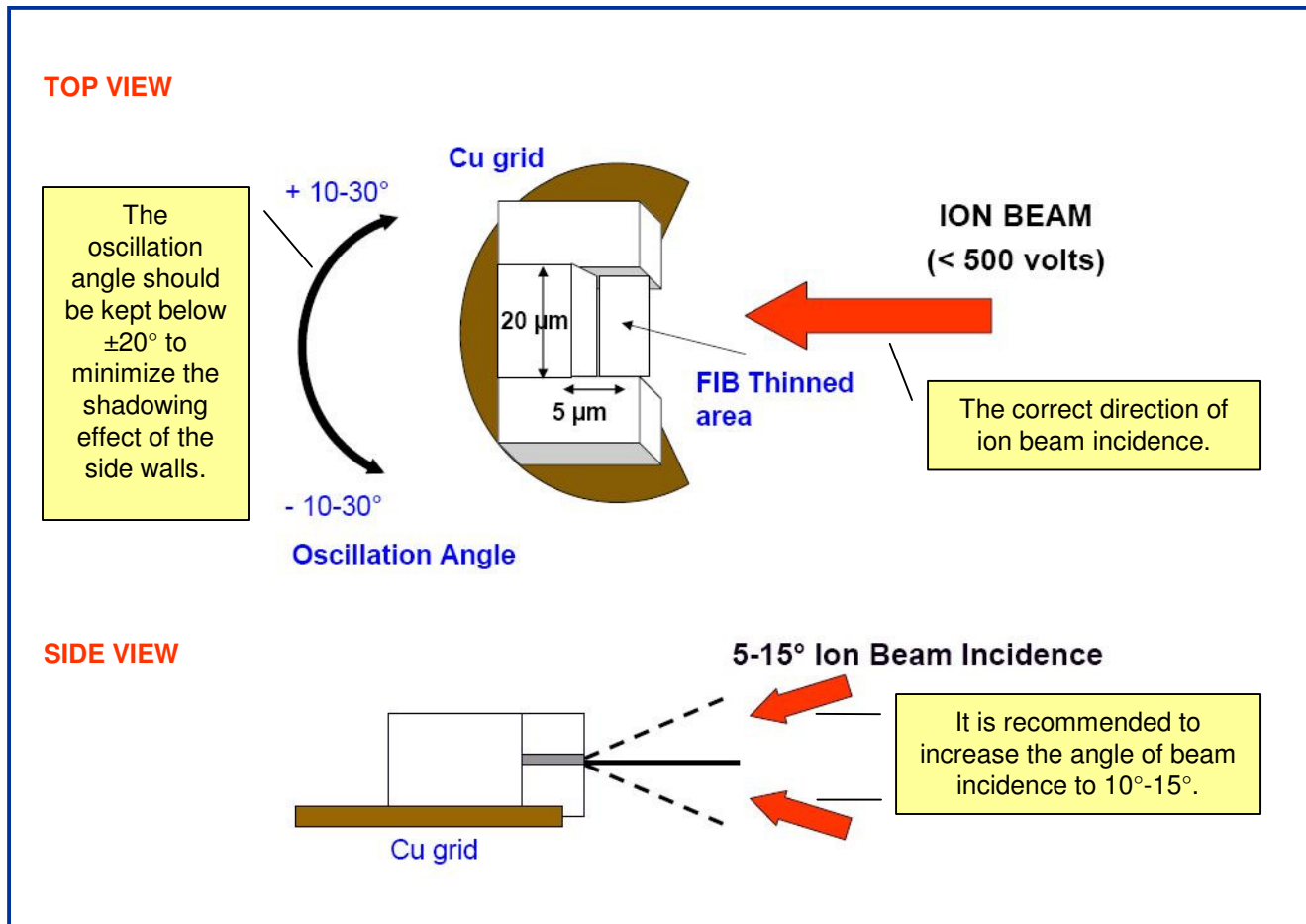
Low-energy ion milling is used for removing the damaged, amorphized surface layer generated by the high-energy Ga⁺ ions during the FIB sample preparation process.

In case of H-bar samples - as a first step of the process - final trimming is performed on both sides of the FIB lamella by medium-energy (around 1000 eV) noble gas ion milling lasting for some minutes. Afterwards, by reducing the ion energy to about 200-300 eV final cleaning is done for a few tens of minutes in order to obtain good quality HRTEM samples. The entire process is completed within 1 hour depending on the parameters of the FIB processing.

Since the Lift-out samples are usually thinner than the H-bar ones, a shorter time of medium-energy ion milling in combination with low-energy cleaning may be sufficient to achieve the desired HRTEM sample quality.

In the following sections recommended low-energy ion milling/cleaning parameters are shown for some possible arrangements of FIB samples mounted on different types of grids.

H-bar samples



Lift-out samples

Illustration of the lift-out technique:

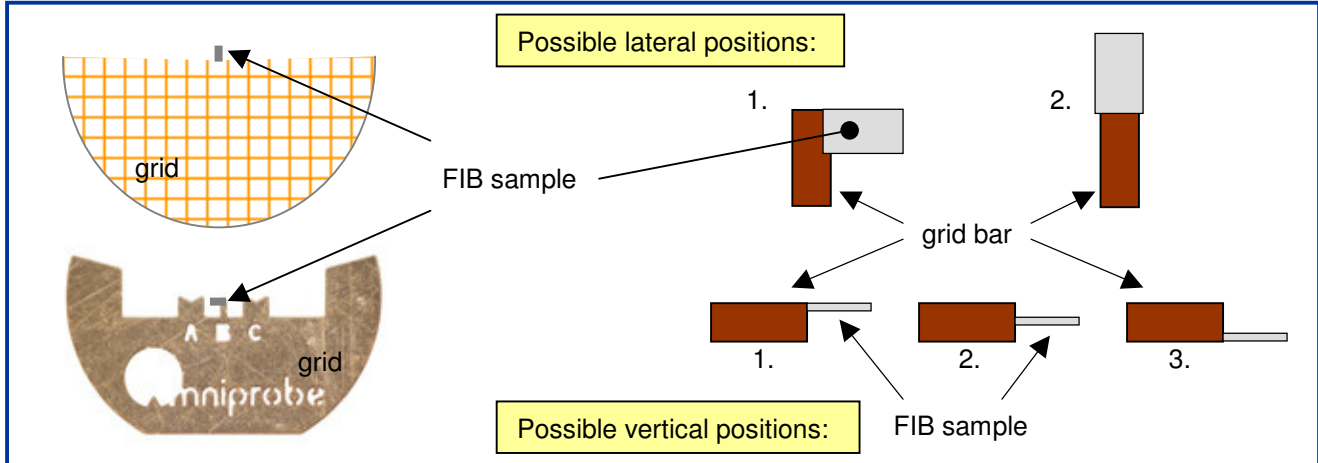
The FIB lamella is welded (fixed) to a grid before further processing. Once the FIB welding process is completed and the lamella is properly fixed to the grid, medium- and low-energy ion milling is performed on the sample using the Technoorg Gentle Mill equipped with a dedicated low-energy ion source.

In order to avoid any re-deposition or sample contamination proper noble gas ion milling conditions should be set. The following parameters should be taken into account in order to find the proper milling conditions for a given arrangement:

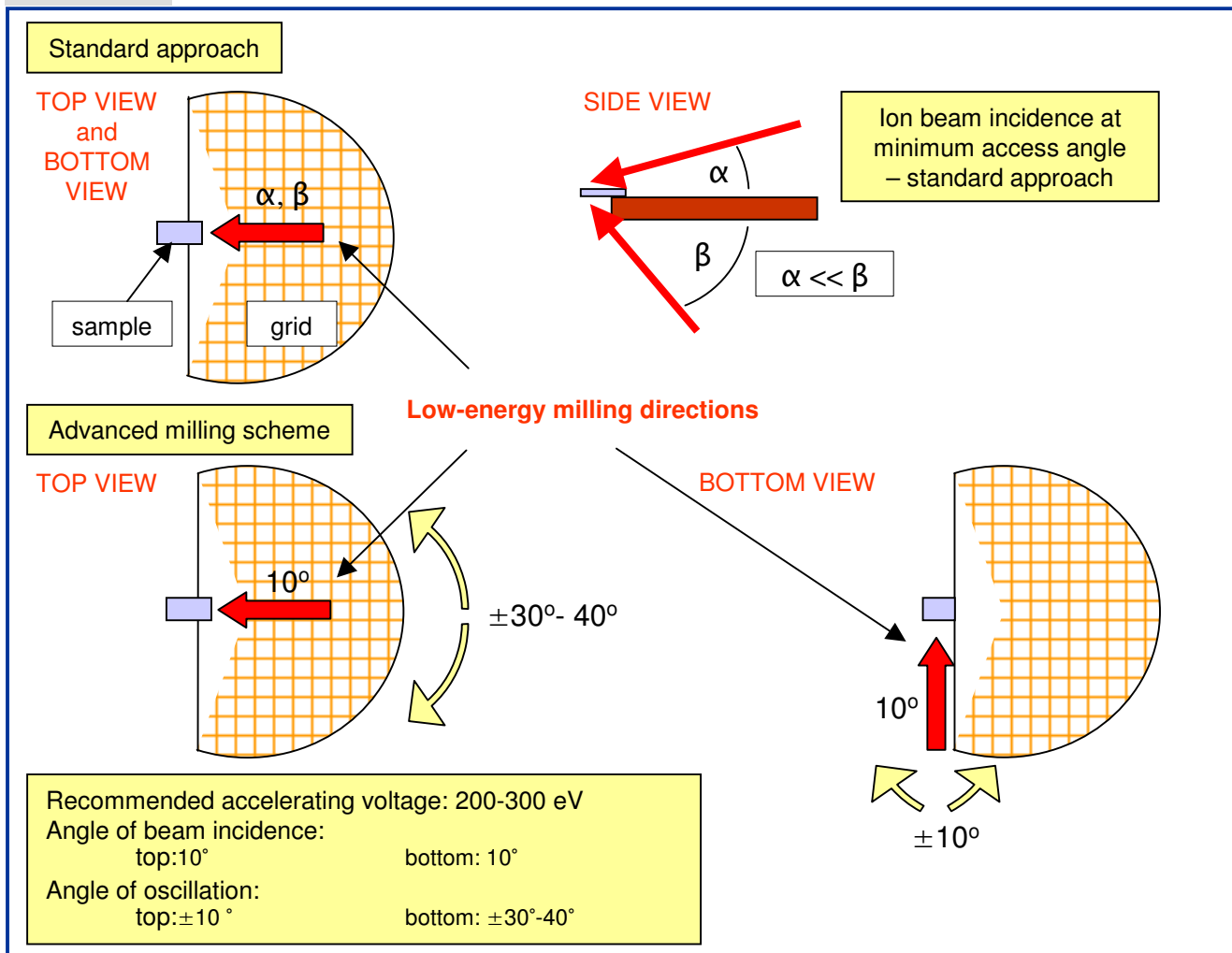
- the geometry and the material of the grid,
- the size and the material of the lamella,
- presence of any protective layer on the lamella and the material of the protective layer,
- the way of sample mounting on the grid.

Lift-out samples

Different mounting positions of the lamella on the grid:

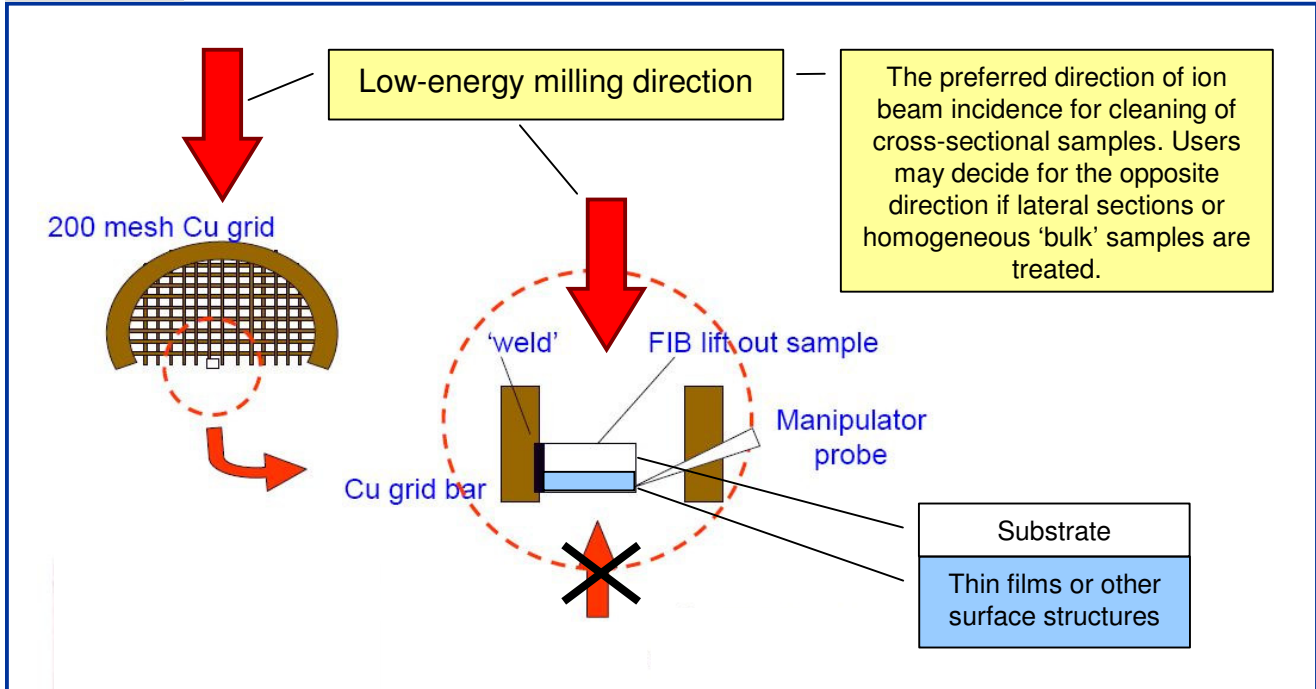


Sample 1

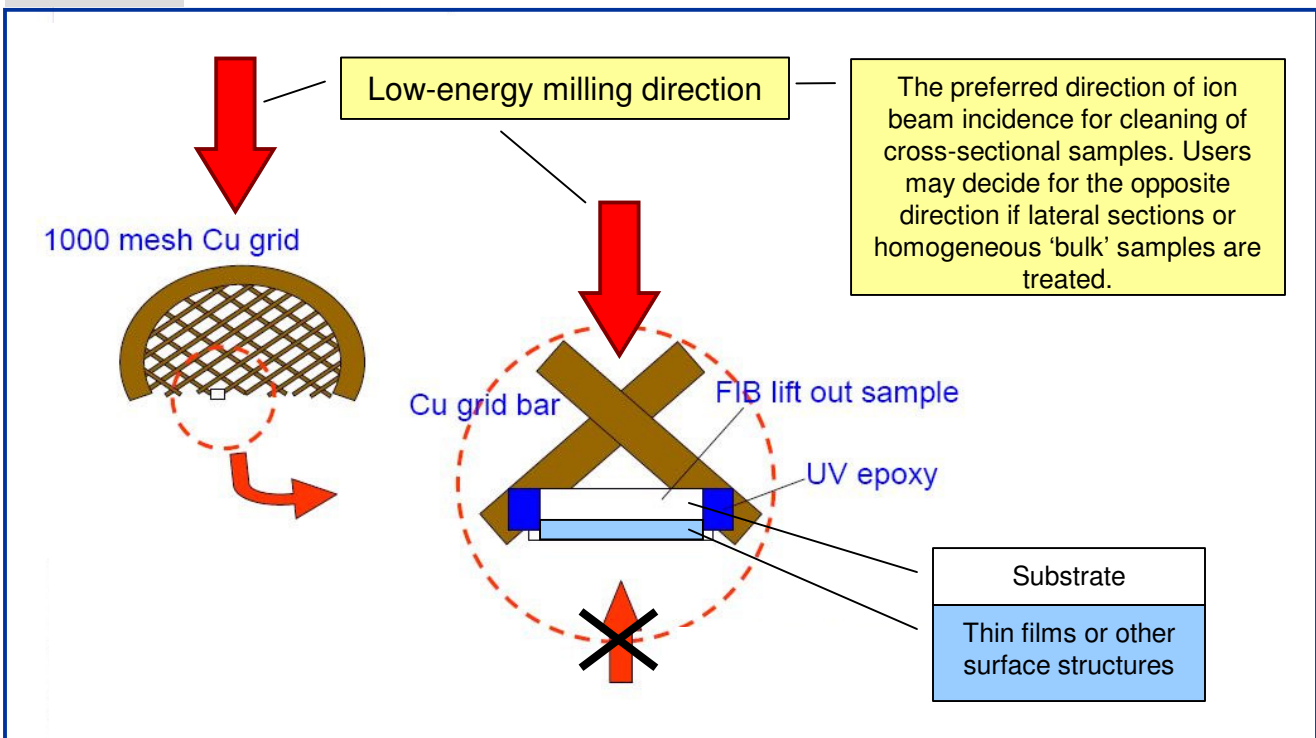


Lift-out samples

Sample 2



Sample 3



Lift-out samples

Sample 4

